

## CORRECTION

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[View Journal](#) | [View Issue](#)**Correction: Optical properties and carrier dynamics in Co-doped ZnO nanorods**Cite this: *Nanoscale Adv.*, 2021, 3, 618

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Correction for 'Optical properties and carrier dynamics in Co-doped ZnO nanorods' by Aswathi K. Sivan *et al.*, *Nanoscale Adv.*, 2021, DOI: 10.1039/d0na00693a.

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The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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